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July 2003

FDS9926A

FAIRCHILD SEMICONDUCTOR®

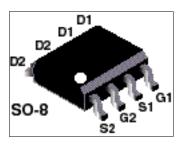
Dual N-Channel 2.5V Specified PowerTrench^o MOSFET

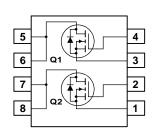
General Description

These N-Channel 2.5V specified MOSFETs use Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 10V).

Applications

- Battery protection
- Load switch
- Power management





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DSS}	Drain-Source Voltage			20	V
V _{GSS}	Gate-Source Voltage			±10	
D	Drain Curre	nt – Continuous	(Note 1a)	6.5	A
		– Pulsed		20	
P _D	Power Dissipation for Dual Operation			2	W
	Power Dissipation for Single Operation (Note 1a)			1.6	
			(Note 1b)	1	
			(Note 1c)	0.9	
Γ _J , T _{STG}	Operating a	nd Storage Junction Temp	erature Range	-55 to +150	°C
Therma	l Charac	teristics	·		
R _{0JA}	Thermal Re	sistance, Junction-to-Ambi	ent (Note 1a)	78	°C/W
S ^{ejc}	Thermal Re	Thermal Resistance, Junction-to-Case (Note 1)		40	
Packag	e Markin	g and Ordering l	nformation		
Device Marking		Device	Reel Size	Tape width	Quantity
FDS9926A		FDS9926A	13"	12mm	2500 units

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Features

6.5 A, 20 V.

$$\begin{split} R_{\text{DS(ON)}} &= 30 \ \text{m}\Omega \ @ \ \text{V}_{\text{GS}} = 4.5 \ \text{V} \\ R_{\text{DS(ON)}} &= 43 \ \text{m}\Omega \ @ \ \text{V}_{\text{GS}} = 2.5 \ \text{V}. \end{split}$$

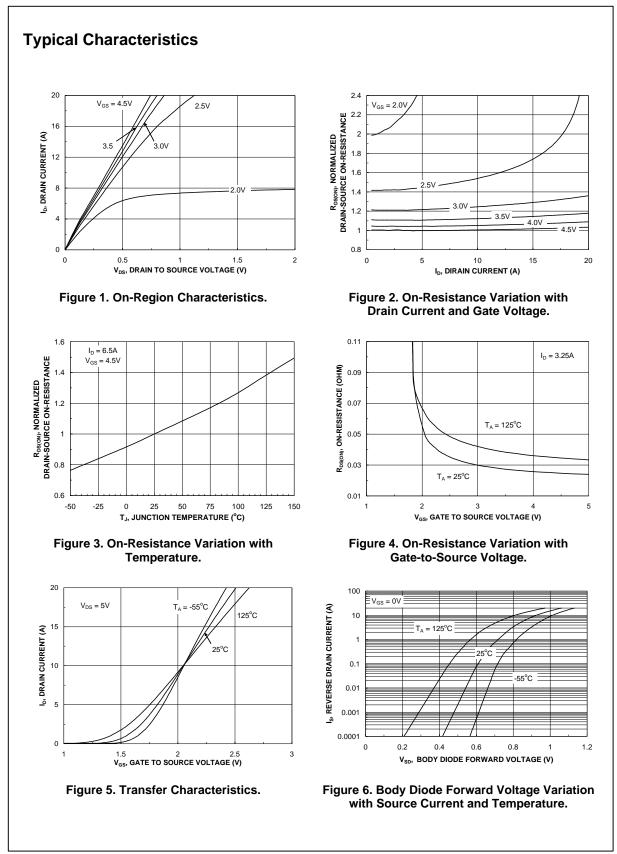
- Optimized for use in battery protection circuits
- Low gate charge

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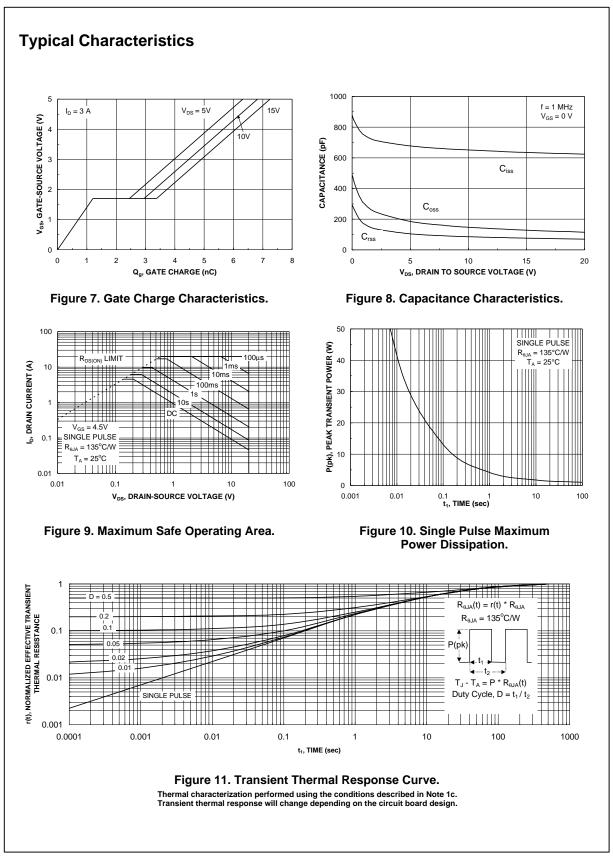
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V$, $I_D = 250 \mu A$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I _{GSS}	Gate–Body Leakage	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_{D} = 250 \ \mu A$	0.6	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{J}}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		-3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{ll} V_{GS} = 4.5 \ V, & I_D = 6.5 \ A \\ V_{GS} = 2.5 \ V, & I_D = 5.4 \ A \\ V_{GS} = 4.5 \ V, \ I_D = 6.5 \ A, \ T_J = 125^\circ C \end{array} $		25 35 35	30 43 50	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	15			Α
g _{FS}	Forward Transconductance	$V_{\text{DS}} = 5 \text{ V}, \qquad I_{\text{D}} = 6.5 \text{ A}$		22		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 10 V$, $V_{GS} = 0 V$,		650		pF
Coss	Output Capacitance	f = 1.0 MHz		150		pF
C _{rss}	Reverse Transfer Capacitance	1		85		pF
R _G	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz		1.4		Ω
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn–On Delay Time	$V_{DD} = 10 V$, $I_D = 1 A$,		8	16	ns
t _r	Turn–On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		9	17	ns
t _{d(off)}	Turn–Off Delay Time	1		15	26	ns
t _f	Turn–Off Fall Time			4	9	ns
Q _g	Total Gate Charge	$V_{DS} = 10 V$, $I_D = 3 A$,		6.2	9	nC
Q _{gs}	Gate–Source Charge	V _{GS} = 4.5 V		1.2		nC
Q _{gd}	Gate-Drain Charge			1.7		nC
Drain-Se	ource Diode Characteristics ar	d Maximum Ratings				
V _{SD}	Drain–Source Diode Forward Voltage			0.73	1.3	V
t _{rr}	Diode Reverse Recovery Time	$I_F = 6.5 \text{ A}, d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		15		nS
Q _{rr}	Diode Reverse Recovery Charge	1		5		nC

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

FDS9926A Rev E (W)



FDS9926A



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Programmable A		POP™	SuperSOT™-3	

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